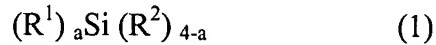


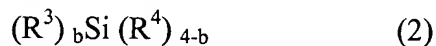
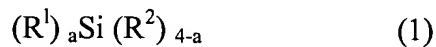
Amendments to the Claims:

1. (original) A composition for forming porous film comprising:
an acid or base generator for generating acid or base by its thermal decomposition and
a polymer which is obtainable by hydrolyzing and condensing one or more silane
compounds represented by Formula (1) :



wherein R^1 represents a straight chain or branched monovalent hydrocarbon having 6 to 20 carbons which may be substituted or unsubstituted and when there are R^1 's, the R^1 's each may be independently same or different; R^2 represents a hydrolysable group and when there are R^2 's, the R^2 's each may be independently same or different; and a is an integer of 1 to 3.

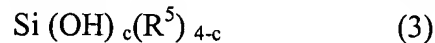
2. (original) A composition for forming porous film comprising:
an acid or base generator for generating acid or base by its thermal decomposition and
a polymer which is obtainable by hydrolyzing and co-condensing one or more silane
compounds represented by Formula (1) and one more silane compounds represented by Formula
(2), Formulas (1) and (2) being:



wherein R^1 represents a straight chain or branched monovalent hydrocarbon having 6 to 20 carbons which may be substituted or unsubstituted and when there are R^1 's, the R^1 's each may be independently same or different; R^2 represents a hydrolysable group and when there are R^2 's, the R^2 's each may be independently same or different; and a is an integer of 1 to 3; R^3 represents a straight chain or branched monovalent hydrocarbon having 1 to 5 carbons which may be substituted or unsubstituted and when there are R^3 's, the R^3 's each may be independently same or different; R^4 represents a hydrolysable group and when there are R^4 's, the R^4 's each may be independently same or different; and b is an integer of 0 to 3.

3. (original) The composition for forming porous film according to Claim 2 wherein
said polymer is a silanol group-containing hydrolysate having number-average molecular weight

of 100 or more, and in said polymer 30 to 80 mol% of structural units derived from said silane compound represented by Formula (2) is represented by Formula (3):

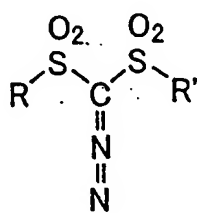


wherein R^5 represents a siloxane residue or R^3 , and c is an integer of 1 or 2.

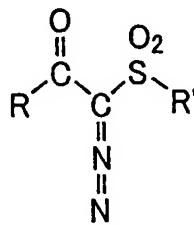
4. (currently amended) The composition for forming porous film according to any one of Claim[[s]] 1 [[to 3]] wherein decomposition temperature of said acid or base generator is lower than decomposition temperature of R1 of said polymer.

5. (original) The composition for forming porous film according to Claim 4 wherein said acid or base generator has decomposition temperature of 250°C or less.

6. (original) The composition for forming porous film according to Claim 5 wherein said acid or base generator is a diazo compound represented by Formula (4) or (5):



(4)



(5)

wherein R and R' each independently represents an alkyl group, an aromatic group, an aralkyl group or a fluoroalkyl group and R and R' may be same or different.

7. (currently amended) A method for forming porous film comprising a step of applying said composition of any one of Claim[[s]] 1 [[to 6]] on a substrate to form a film and a step of transforming the film into porous film.

8. (original) The method for forming porous film according to Claim 7 wherein said step of transforming comprises a step of drying the film and a step of forming pores in the dried film.

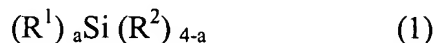
9. (currently amended) The method for forming porous film according to Claim 7 [[or 8]] wherein said step of transforming comprises the thermal treatment of 170 to 400°C.

10. (currently amended) A porous film obtainable from said composition according to ~~any one of~~ Claim[[s]] 1 [[to 6]].

11. (currently amended) An interlevel insulator film formable by said composition according to ~~any one of~~ Claim[[s]] 1 [[to 6]].

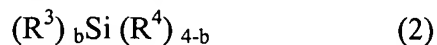
12. (original) A semiconductor device comprising an internal porous film formed by a composition comprising an acid or base generator for generating acid or base by its thermal decomposition and a polymer obtainable from one or more silane compounds.

13. (original) The semiconductor device according to Claim 12 wherein said polymer is obtainable by hydrolyzing and condensing one or more silane compounds represented by Formula (1):



wherein R^1 represents a straight chain or branched monovalent hydrocarbon having 6 to 20 carbons which may be substituted or unsubstituted and when there are R^1 's, the R^1 's each may be independently same or different; R^2 represents a hydrolysable group and when there are R^2 's, the R^2 's each may be independently same or different; and a is an integer of 1 to 3.

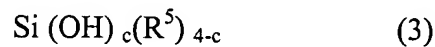
14. (original) The semiconductor device according to Claim 12 wherein said polymer is obtainable by hydrolyzing and co-condensing one or more silane compounds represented by Formula (1) and one more silane compounds represented by Formula (2), Formulas (1) and (2) being:



wherein R^1 represents a straight chain or branched monovalent hydrocarbon having 6 to 20 carbons which may be substituted or unsubstituted and when there are R^1 's, the R^1 's each may be independently same or different; R^2 represents a hydrolysable group and when there are R^2 's, the R^2 's each may be independently same or different; and a is an integer of 1 to 3; R^3 represents a

straight chain or branched monovalent hydrocarbon having 1 to 5 carbons which may be substituted or unsubstituted and when there are R^3 's, the R^3 's each may be independently same or different; R^4 represents a hydrolysable group and when there are R^4 's, the R^4 's each may be independently same or different; and b is an integer of 0 to 3.

15. (original) The semiconductor device according to Claim 14 wherein said polymer is a silanol group-containing hydrolysate having number-average molecular weight of 100 or more, and in said polymer 30 to 80 mol% of structural units derived from said silane compound represented by Formula (2) is represented by Formula (3):

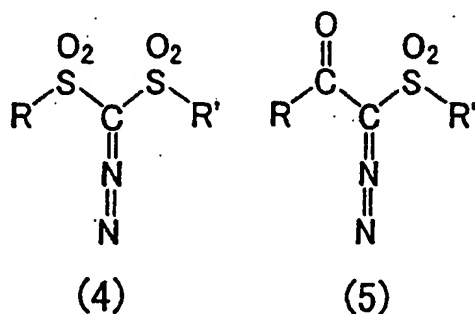


wherein R^5 represents a siloxane residue or R^3 , and c is an integer of 1 or 2.

16. (currently amended) The semiconductor device according to any one of Claim[[s]] 13 [[to 15]] wherein decomposition temperature of said acid or base generator is lower than decomposition temperature of R^1 of said polymer.

17. (original) The semiconductor device according to Claim 16 wherein said acid or base generator has decomposition temperature of 250°C or less.

18. (original) The semiconductor device according to Claim 17 wherein said acid or base generator is a diazo compound represented by Formula (4) or (5):



wherein R and R' each independently represents an alkyl group, an aromatic group, an aralkyl group or a fluoroalkyl group and R and R' may be same or different.

19. (currently amended) The semiconductor device according to ~~any one of~~ Claim[[s]] 12 [[to 18]] wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.